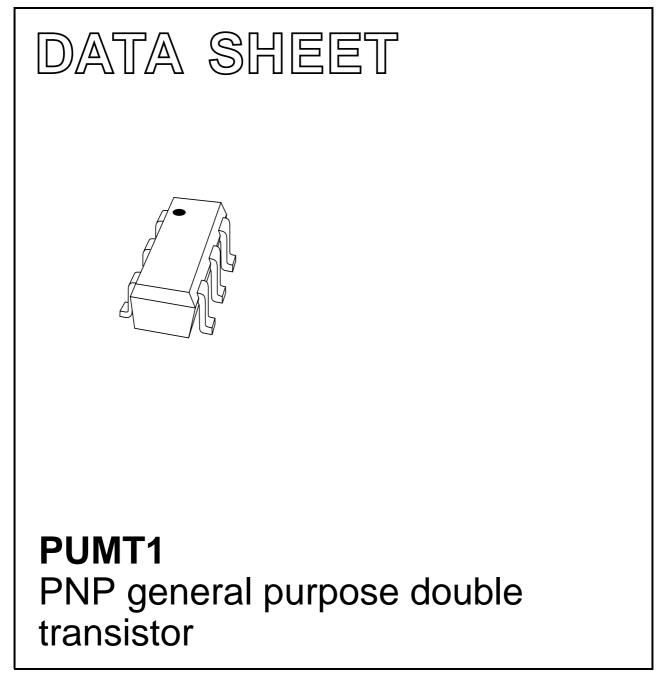
DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 1999 Apr 14 2001 Dec 19



PNP general purpose double transistor

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 40 V)
- Reduces number of components and boardspace.

APPLICATIONS

• General purpose switching and amplification.

DESCRIPTION

Two independently operating PNP transistors in an SC-88; SOT363 plastic package. NPN complement: PUMX1.

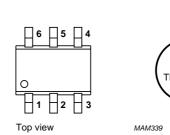
MARKING

TYPE NUMBER	MARKING CODE	
PUMT1	FtF	

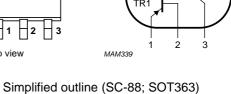
PINNING

Fig.1

PIN	DESCRIPTION	
1, 4	emitter	TR1; TR2
2, 5	base	TR1; TR2
3, 6	collector	TR2; TR1



and symbol.



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER CONDITIONS		MIN.	MAX.	UNIT		
Per transist	Per transistor						
V _{CBO}	collector-base voltage	open emitter	_	-50	V		
V _{CEO}	collector-emitter voltage	open base	_	-40	V		
V _{EBO}	emitter-base voltage	open collector	—	-5	V		
I _C	collector current (DC)		_	-100	mA		
I _{CM}	peak collector current		_	-200	mA		
I _{BM}	peak base current		_	-200	mA		
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	_	200	mW		
T _{stg}	storage temperature		-65	+150	°C		
Tj	junction temperature		_	150	°C		
T _{amb} operating ambient temperature			-65	+150	°C		
Per device			L				
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$; note 1	_	300	mW		

2

Note

1. Device mounted on an FR4 printed-circuit board.

PUMT1

TR2

PNP general purpose double transistor

PUMT1

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT	
Per device					
R _{th j-a}	thermal resistance from junction to ambient	note 1	416	K/W	

Note

1. Device mounted on an FR4 printed-circuit board.

CHARACTERISTICS

 T_{amb} = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transist	tor				
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = -30 V	_	-100	nA
		$I_E = 0; V_{CB} = -30 V; T_j = 150 °C$	-	-10	μA
I _{EBO}	emitter cut-off current	$I_{C} = 0; V_{EB} = -4 V$	_	-100	nA
h _{FE}	DC current gain	$I_{C} = -1 \text{ mA}; V_{CE} = -6 \text{ V}$	120	_	
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = 50 \text{ mA}; I_{B} = -5 \text{ mA}; \text{ note } 1$	-	-200	mV
Cc	collector capacitance	$I_E = i_e = 0; V_{CB} = -12 V; f = 1 MHz$	_	2.2	pF
f _T	transition frequency	$I_{C} = -2 \text{ mA}; V_{CE} = -12 \text{ V}; \text{ f} = 100 \text{ MHz}$	100	_	MHz

Note

1. Pulse test: $t_p \leq 300~\mu s;~\delta \leq 0.02.$

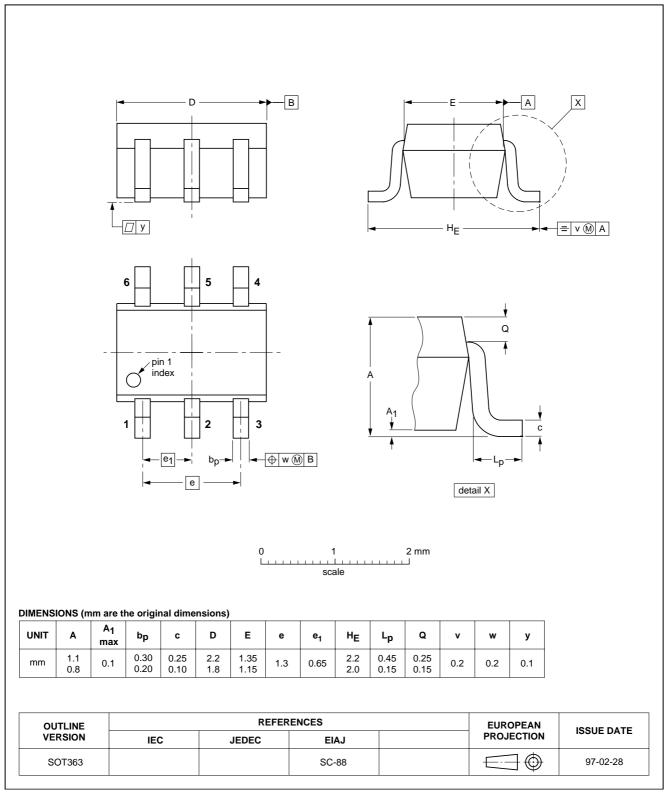
Product data sheet

PUMT1

PNP general purpose double transistor

PACKAGE OUTLINE





SOT363

PNP general purpose double transistor

PUMT1

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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